

RAA23040x

R18DS0004EJ0102

Rev.1.02

Jul.09, 2013

3-ch Step-Down Switching Regulator + 1-ch LDO

Description

The RAA23040x is a power supply IC that has 3-ch step-down Switching Regulator containing power MOSFETs and 1-ch LDO.

Features

- Switching Regulator (ch1, ch3, ch4)
 - Synchronous rectification type step-down circuit
 - Integrated power MOSFETs
 - Internal phase compensator
 - Power good function (ch1)
 - Low power mode
(ch1, ch3 and ch4 operate at low frequency and reduce the power consumption of the IC.)
 - Switching frequency: 1.3 MHz to 2 MHz (variable)
 - Internal timer-latch-type short-circuit protector
- LDO (ch2)
 - Internal over current protector (foldback-current limiting)
- Common part
 - Independent On/Off control for each channel
 - Internal digital soft-start function (adjustable soft-start time)
 - Internal discharge circuit
 - Internal timer-latch-type thermal shutdown circuit (shutdown temperature: 150°C or higher)
 - Internal recovery-type under voltage lockout circuit

PKG and Packing

| Part No. | Package | Packing |
|--------------|-------------|--------------------------------|
| RAA23040xGNP | 32-pin VQFN | Embossed taping. 4,000pcs/reel |
| RAA23040xGFT | 32-pin TQFP | Tray. 1,250pcs/Inner box |

Product Lineup Table

The following 9 products are developed based on output voltage.

| ch | RAA230401 | RAA230402 | RAA230403 | RAA230404 | RAA230405 | RAA230406 | RAA230407 | RAA230408 | RAA230409 |
|----|---|-----------|-----------|-----------|------------|-----------|-----------|-----------|------------|
| 1 | 1.8 V | 2.5 V | 3.0 V | 3.3 V | 1.8 V | 2.5 V | 3.0 V | 3.3 V | Adjustable |
| 2 | | | | | | | | | |
| 3 | 3.3 V | | | | Adjustable | | | | |
| 4 | Output voltage is selectable. 1.2 V preset voltage by internal resistor or adjustable by external resistor. | | | | | | | | |

Note: ch1, ch2: RAA230401 to RAA230408 output preset voltage by internal resistor. RAA230409 outputs adjustable voltage by external resistor.

ch3: RAA230401 to RAA230404 output preset voltage by internal resistor. RAA230405 to RAA230409 output adjustable voltage by external resistor.

ch4: All products have switchable output voltage between 1.2 V preset voltage by internal resistor and adjustable voltage by external resistor.

Constitution Example

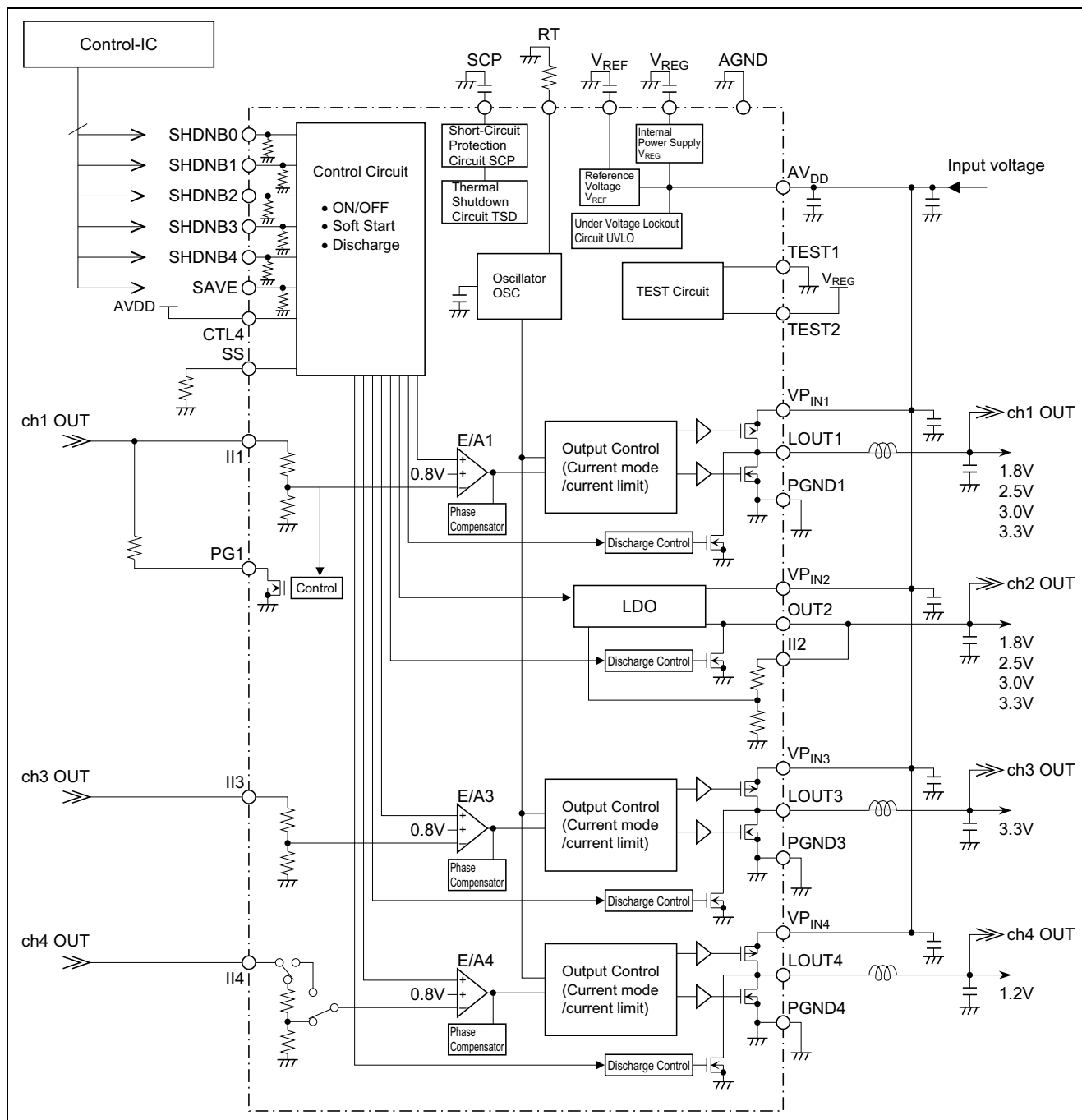
- Input Voltage: 2.5 V to 5.5 V

| ch | Type | Power MOSFET | Output Voltage | Maximum Output Current Example |
|----|---|--------------|--------------------------------|--------------------------------|
| 1 | Synchronous rectification type step-down circuit (Current mode) | Integrated | 0.9 V to $V_{IN} \times 0.8$ V | 500 mA |
| 2 | LDO | — | 0.9 V to $V_{IN} \times 0.8$ V | 100 mA |
| 3 | Synchronous rectification type step-down circuit (Current mode) | Integrated | 0.9 V to $V_{IN} \times 0.8$ V | 1500 mA |
| 4 | Synchronous rectification type step-down circuit (Current mode) | Integrated | 0.9 V to $V_{IN} \times 0.8$ V | 1500 mA |

Application Circuit Example

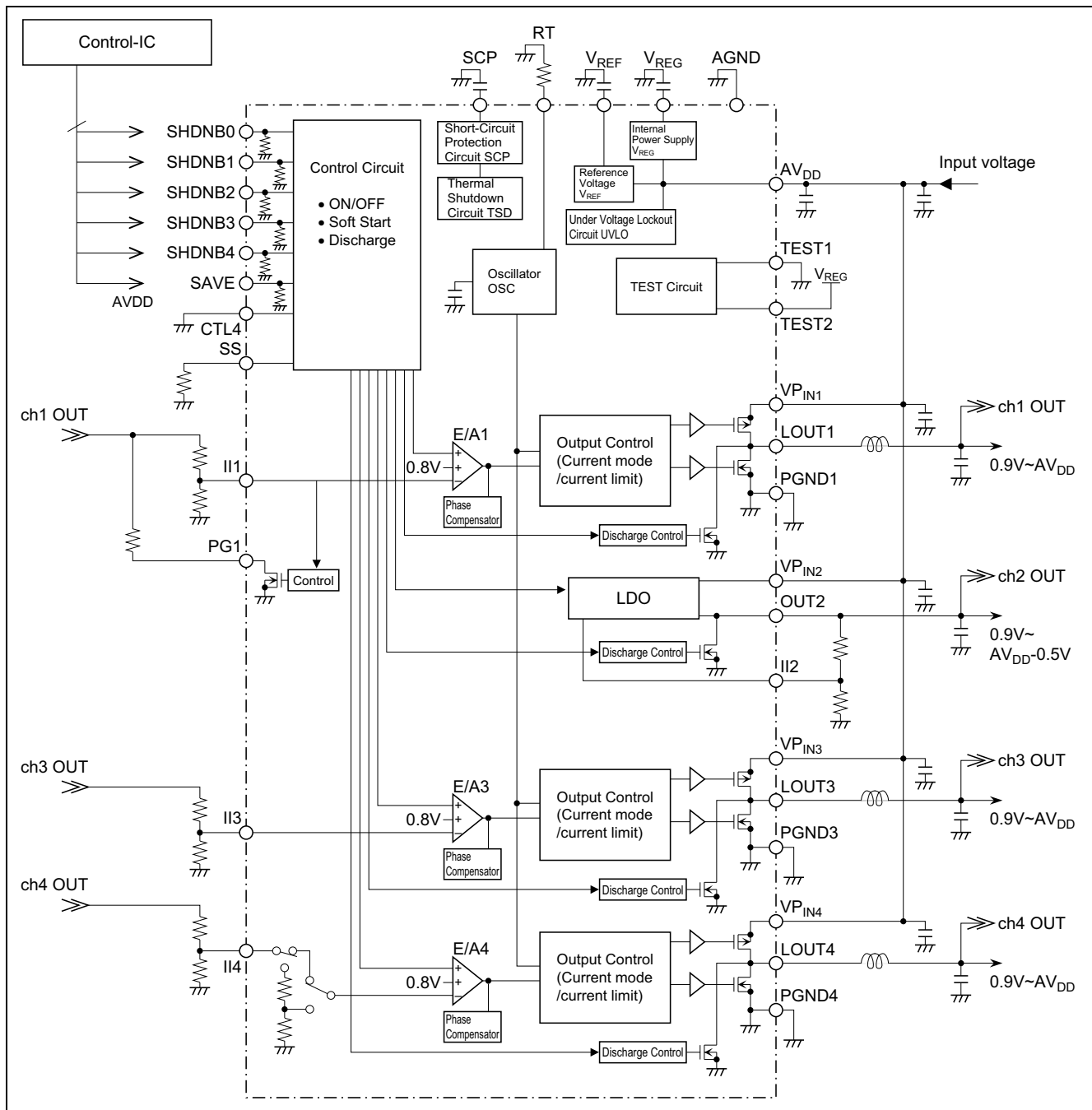
ch1 to ch3: Preset output voltage by internal resistor.

ch4: Preset output voltage by internal resistor is selected. (CTL4 = H)



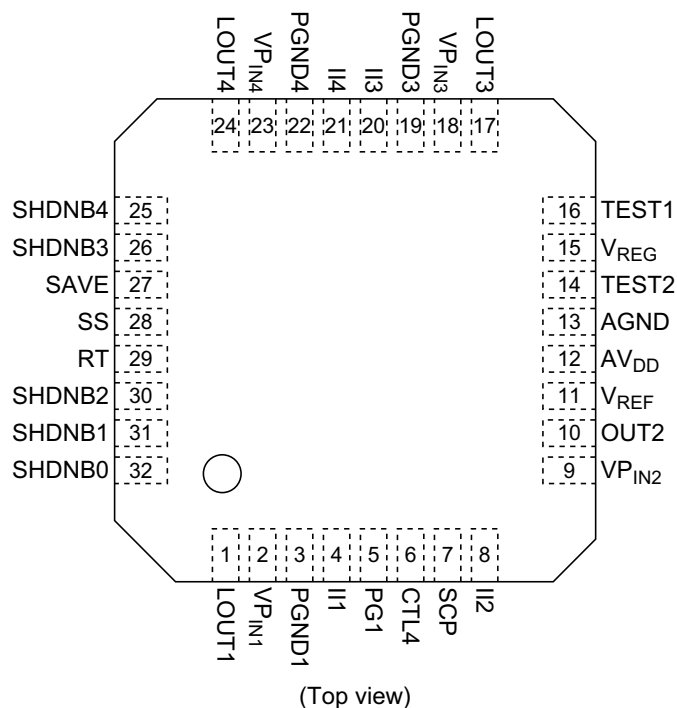
ch1 to ch3: Adjustable output voltage by external resistor.

ch4: Adjustable output voltage by external resistor is selected. (CTL4 = L)

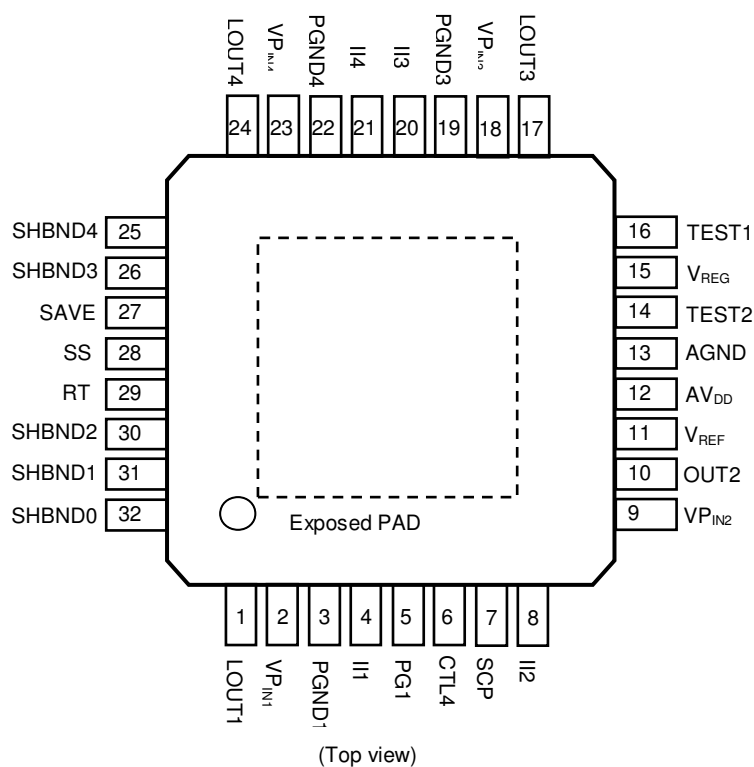


Pin Configuration

32-pin VQFN



32-pin TQFP



Pin Function

| Pin No. | Symbol | I/O | Function |
|---------|-------------------|--------------|--|
| 1 | LOUT1 | Output | Inductor connection for ch1 |
| 2 | VP _{IN1} | Power supply | Output stage power input of ch1 |
| 3 | PGND1 | Ground | Power ground |
| 4 | II1 | Input | Inverted input for error amplifier of ch1 |
| 5 | PG1 | Output | Power-good output of ch1 (open-drain) |
| 6 | CTL4 | Input | Output voltage setting mode of ch4 |
| 7 | SCP | — | Capacitor connection pin for timer latch |
| 8 | II2 | Input | Inverted input for error amplifier of ch2 |
| 9 | VP _{IN2} | Power supply | Output stage power input of ch2 |
| 10 | OUT2 | Output | Output of ch2 |
| 11 | V _{REF} | Output | Reference voltage output |
| 12 | AV _{DD} | Power supply | Analog block power supply |
| 13 | AGND | Ground | Analog ground |
| 14 | TEST2 | — | Test pin 2 (connect to V _{REG}) |
| 15 | V _{REG} | Output | Internal power supply output |
| 16 | TEST1 | — | Test pin 1 (connect to AGND) |
| 17 | LOUT3 | Output | Inductor connection for ch3 |
| 18 | VP _{IN3} | Power supply | Output stage power input of ch3 |
| 19 | PGND3 | Ground | Power ground |
| 20 | II3 | Input | Inverted input for error amplifier of ch3 |
| 21 | II4 | Input | Inverted input for error amplifier of ch4 |
| 22 | PGND4 | Ground | Power ground |
| 23 | VP _{IN4} | Power supply | Output stage power input of ch4 |
| 24 | LOUT4 | Output | Inductor connection for ch4 |
| 25 | SHDNB4 | Input | Output ON/OFF of ch4 |
| 26 | SHDNB3 | Input | Output ON/OFF of ch3 |
| 27 | SAVE | Input | Low power operation mode setting pin |
| 28 | SS | — | Resistance connection for soft start time setting |
| 29 | RT | — | Resistance connection for triangular wave generation |
| 30 | SHDNB2 | Input | Output ON/OFF of ch2 |
| 31 | SHDNB1 | Input | Output ON/OFF of ch1 |
| 32 | SHDNB0 | Input | Output ON/OFF of IC |

Absolute Maximum Ratings

(Unless otherwise specified, $T_A = 25^\circ\text{C}$)

| Parameter | Symbol | Ratings | Unit | Condition |
|--|-------------------------|--------------------------|------------------|--------------------------------------|
| Analog power supply (AV_{DD} pin) | AV_{DD} | -0.5 to +6.5 | V | AV_{DD} |
| VP_{IN} pin applied voltage | VP_{IN} | -0.5 to +6.5 | V | VP_{IN1} to VP_{IN4} |
| SHDNB pin applied voltage | V_{SHDNB} | -0.5 to +6.5 | V | SHDNB0 to SHDNB4 |
| CTL4 pin applied voltage | V_{CTL4} | -0.5 to +6.5 | V | CTL4 |
| SAVE pin applied voltage | V_{SAVE} | -0.5 to +6.5 | V | SAVE |
| PG pin applied voltage | V_{PG} | -0.5 to +6.5 | V | PG1 |
| II pin applied voltage | V_{II} | -0.5 to +6.5 | V | II1 to II4 |
| VP_{IN1} pin sink current (peak) | $IP_{IN1(peak)-}$ | 600 | mA | VP_{IN1} |
| VP_{IN2} pin sink current (DC) | $IP_{IN2(DC)-}$ | 200 | mA | VP_{IN2} |
| VP_{IN3} pin sink current (peak) | $IP_{IN3(peak)-}$ | 2000 | mA | VP_{IN3} |
| VP_{IN4} pin sink current (peak) | $IP_{IN4(peak)-}$ | 2000 | mA | VP_{IN4} |
| LOUT1 pin output source current (peak) | $I_{LO1(peak)+}$ | 600 | mA | LOUT1 |
| OUT2 pin output source current (DC) | $I_{O2(DC)+}$ | 200 | mA | OUT2 |
| LOUT3 pin output source current (peak) | $I_{LO3(peak)+}$ | 2000 | mA | LOUT3 |
| LOUT4 pin output source current (peak) | $I_{LO4(peak)+}$ | 2000 | mA | LOUT4 |
| LOUT1, OUT2, LOUT3, LOUT4 pin output source current (DC) | $I_{LO1,O2,LO3,4(DC)-}$ | 100 | mA | when discharge circuit is operation. |
| Total power dissipation | P_T | VQFN: 1850 ^{*1} | mW | $T_A \leq +25^\circ\text{C}$ |
| | | TQFP: 2100 ^{*1} | | |
| Operating ambient temperature | T_A | -40 to +85 | $^\circ\text{C}$ | |
| Junction temperature | T_J | -40 to +150 | $^\circ\text{C}$ | |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ | |

Note:

*1 This is the value at $T_A \leq +25^\circ\text{C}$. At $T_A > +25^\circ\text{C}$,

the total power dissipation is derated by $-18.5 \text{ mW}/^\circ\text{C}$ (VQFN) or $-21 \text{ mW}/^\circ\text{C}$ (LQFP).

Board specification: VQFN: 4-layers glass epoxy board. 76.2mm x 114.3mm x 1.664mm.

Copper coverage area: 50% (top and bottom layers)/95% (layers 2 and 3).

TQFP: 4-layers glass epoxy board. 80mm x 80mm x 1.6mm. Renesas Evaluation Board

for the case of that Exposed PAD is not soldered to GND copper pattern on board.

Caution: Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Recommended Operating Condition

(Unless otherwise specified, $T_A = 25^\circ\text{C}$)

| Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|---|-------------|------|-----------|-----------|------------------|--------------------------|
| Analog power supply voltage (AV_{DD} pin) | AV_{DD} | 2.5 | 5.0 | 5.5 | V | AV_{DD} |
| VP_{IN} pin applied voltage | VP_{IN} | — | AV_{DD} | — | V | VP_{IN1} to VP_{IN4} |
| SHDNB pin applied voltage | V_{SHDNB} | 0 | — | AV_{DD} | V | SHDNB0 to SHDNB4 |
| CTL4 pin applied voltage | V_{CTL4} | 0 | — | AV_{DD} | V | CTL4 |
| SAVE pin applied voltage | V_{SAVE} | 0 | — | AV_{DD} | V | SAVE |
| PG pin applied voltage | V_{PG} | 0 | — | AV_{DD} | V | PG1 |
| II pin applied voltage | V_{II} | 0 | — | AV_{DD} | V | II1 to II4 |
| Oscillation frequency | f_{OSC} | 1300 | — | 2200 | kHz | |
| Oscillator timing resistance | R_T | — | 10 | — | $k\Omega$ | R_T |
| Soft start resistance | R_{SS} | — | 1000 | — | $k\Omega$ | SS |
| SCP pin capacitance | C_{SCP} | — | 0.1 | — | μF | SCP |
| V_{REF} pin capacitance | C_{REF} | — | 1.0 | — | μF | V_{REF} |
| V_{REG} pin capacitance | C_{REG} | — | 1.0 | — | μF | V_{REG} |
| Operating junction temperature | T_{JO} | -40 | — | +125 | $^\circ\text{C}$ | |

Electrical Characteristics

(Unless otherwise specified, $T_A = 25^\circ\text{C}$, $AV_{DD} = VP_{IN1}$ to $VP_{IN4} = 5.0\text{ V}$, $f_{OSC} = 2\text{ MHz}$)

| | Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|--|--|------------------|-------|-------|-------|---------------|--|
| Total | Standby current | $I_{DD(STNBY)}$ | — | 1 | 2 | μA | $AI_{DD} + IP_{IN1} + IP_{IN2} + IP_{IN3} + IP_{IN4}$ SHDNB0 to SHDNB4 = AGND |
| | Circuit operation current 1 | I_{DD1} | — | 1.2 | 2 | mA | AI_{DD} , SHDNB0 = AV_{DD} SHDNB1 to SHDNB4 = AGND SAVE = GND |
| | Circuit operation current 2 | I_{DD2} | — | 0.7 | 1.0 | mA | AI_{DD} , SHDNB0 = AV_{DD} SHDNB1 to SHDNB4 = AGND SAVE = AV_{DD} |
| Reference voltage block (V_{REF}) | Reference voltage | V_{REF} | 0.98 | 1.00 | 1.02 | V | $I_{REF} = 0\text{mA}$ |
| | Temperature characteristic | | — | 0.5 | — | % | $T_A = -10^\circ\text{C}$ to $+60^\circ\text{C}$ |
| Internal power supply block (V_{REG}) | Internal power supply voltage | V_{REG} | 2.3 | 2.4 | 2.5 | V | $I_{REG} = 0\text{mA}$ |
| Under voltage lock out circuit (UVLO) | Operation start voltage during rise time | $AV_{DD(L-H)}$ | 1.9 | 2.1 | 2.3 | V | AV_{DD} pin voltage is detected |
| | Operation stop voltage | $AV_{DD(H-L)}$ | 1.7 | 1.9 | 2.1 | V | AV_{DD} pin voltage is detected |
| Short-circuit protection circuit (SCP) | II1 input detection voltage (ch1) | $V_{TH(II)1}$ | 65 | 75 | 85 | % | II1 pin, Ratio to the output voltage |
| | II3 input detection voltage (ch3) | $V_{TH(II)3}$ | 65 | 75 | 85 | % | II3 pin, Ratio to the output voltage |
| | II4 input detection voltage (ch4) | $V_{TH(II)4}$ | 65 | 75 | 85 | % | II4 pin, Ratio to the output voltage |
| | DLY detection voltage | $V_{TH(DLY)}$ | 0.6 | 0.9 | 1.2 | V | SCP pin |
| | Short-circuit source current | I_{OUT} | 0.6 | 1.0 | 1.4 | μA | |
| Oscillation block | Frequency setting accuracy | f_{OSC} | -10 | — | +10 | % | $R_T = 10\text{k}\Omega$ |
| | Input stability | Δf_{OSC} | -3 | — | +3 | % | $AV_{DD} = 2.5\text{V}$ to 5.5V |
| Soft start block | Soft start time | t_{ss} | — | 2.0 | 4.0 | ms | ch1 to ch4, $R_{SS} = 1000\text{k}\Omega$ |
| PWM block | Maximum duty | $D_{MAX(PWM)}$ | — | 100 | — | % | ch1, ch3, ch4 |
| Output voltage accuracy (with resistor inside) | ch1 output voltage accuracy | V_{OUT1} | -2 | — | +2 | % | $I_{O1} = 10\text{mA}$, (with internal resistor) |
| | ch2 output voltage accuracy | V_{OUT2} | -1 | — | +1 | % | $I_{O2} = 10\text{mA}$, (with internal resistor) |
| | ch3 output voltage accuracy | V_{OUT3} | -2 | — | +2 | % | $I_{O3} = 200\text{mA}$, (with internal resistor) |
| | ch4 output voltage accuracy | V_{OUT4} | -2 | — | +2 | % | $I_{O4} = 200\text{mA}$, (with internal resistor) |
| E/A block (with resistor outside) | E/A 1 input threshold voltage | V_{ITH1} | 0.784 | 0.800 | 0.816 | V | Including input offset, (with external resistor) |
| | E/A 2 input threshold voltage | V_{ITH2} | 0.792 | 0.800 | 0.808 | V | Including input offset, (with external resistor) |
| | E/A 3 input threshold voltage | V_{ITH3} | 0.784 | 0.800 | 0.816 | V | Including input offset, (with external resistor) |
| | E/A 4 input threshold voltage | V_{ITH4} | 0.784 | 0.800 | 0.816 | V | Including input offset, (with external resistor) |
| Output block (ch1) | P-ch output ON resistance | R_{on-p1} | — | 0.4 | 0.6 | Ω | $I_O = 100\text{mA}$ |
| | N-ch output ON resistance | R_{on-n1} | — | 0.4 | 0.6 | Ω | $I_O = -100\text{mA}$ |
| Output block (ch3, ch4) | P-ch output ON resistance | R_{on-p1} | — | 0.4 | 0.6 | Ω | $I_O = 100\text{mA}$ |
| | N-ch output ON resistance | R_{on-n1} | — | 0.4 | 0.6 | Ω | $I_O = -100\text{mA}$ |
| Discharging circuit block | Output ON resistance1 | R_{ondc1} | — | 100 | 200 | Ω | ch1, ch3, ch4, $I_{DC} = 20\text{mA}$ |
| | Output ON resistance2 | R_{ondc2} | — | 200 | 400 | Ω | ch2, $I_{DC} = 20\text{mA}$ |

Electrical Characteristics (cont.)

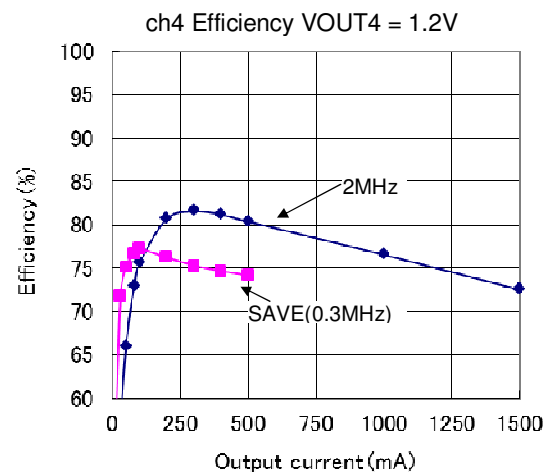
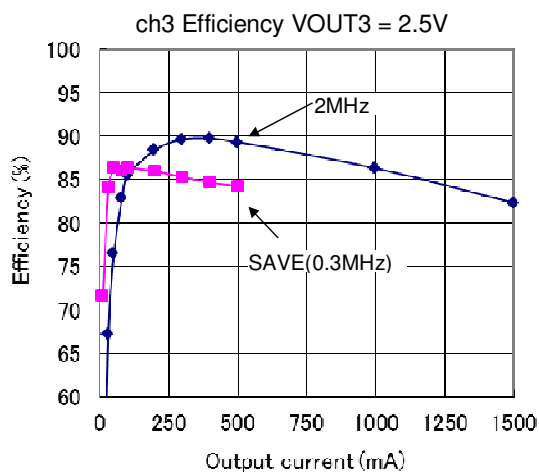
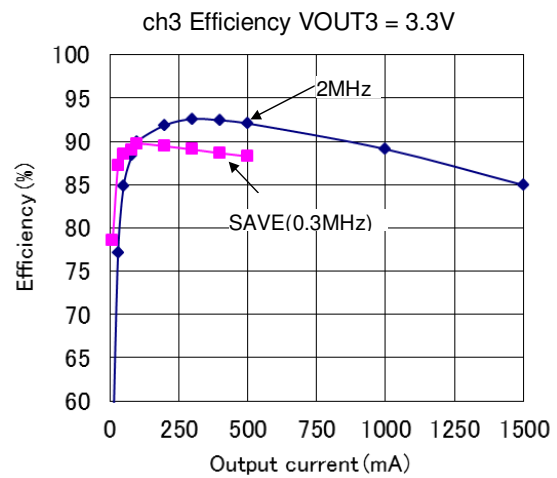
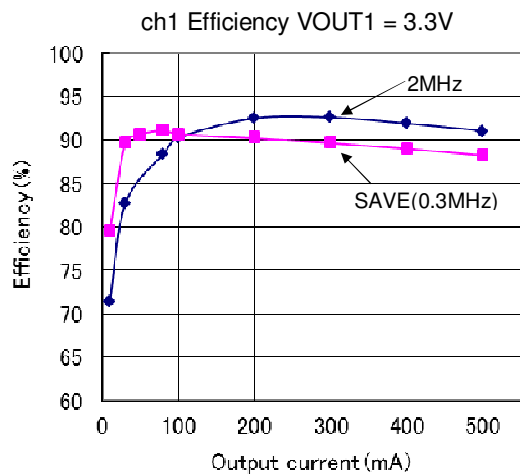
(Unless otherwise specified, $T_A = 25^\circ\text{C}$, $AV_{DD} = VP_{IN1}$ to $VP_{IN4} = 5.0\text{ V}$, $f_{OSC} = 2\text{ MHz}$)

| | Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|--------------------------------|--|---------------|-----|-----|-----|---------------|---|
| Series regulator block (ch2) | The voltage between the input and output | V_{DIF2} | 0.5 | — | — | V | $I_{O2} = 20\text{mA}$ |
| | Input regulation | REG_{IN2} | — | — | 50 | mV | $I_{O2} = 20\text{mA}$, $VP_{IN2} > V_{OUT2} + 0.5\text{V}$ |
| | Load regulation | REG_{L2} | — | — | 50 | mV | $I_{O2} = 1\text{mA}$ to 100mA |
| | Output short-circuit current | $I_{O2short}$ | — | 80 | — | mA | $OUT2 = AGND$ |
| | Peak output current | I_{O2peak} | 150 | — | — | mA | T.B.D. |
| Power-good circuit block (ch1) | Threshold voltage | $V_{TH(PG)1}$ | 86 | 90 | 94 | % | PG1 = "HiZ" → "L", "L" → "HiZ" Detection of I11 pin Ratio to the output voltage |
| | PG pin output voltage | V_{PG} | — | — | 0.1 | V | $I_{PG-} = 0.1\text{mA}$ |
| | PG pin leakage current | $I_{LEAK-PG}$ | — | — | 1 | μA | $SHDNB0$ to $SHDNB4 = AGND$ |
| | Delay time | t_{DLY-PG} | — | — | 2 | ms | Time from detecting of output startup until change from L to HiZ on PG pin |
| ON/OFF controller block | Threshold voltage | V_{TH} | 0.8 | — | 2.0 | V | $SHDNB0$ to $SHDNB4$, SAVE |
| | Input pull-down resistance | R_{IND} | 200 | 400 | 700 | $k\Omega$ | $SHDNB0$ to $SHDNB4$, SAVE |

Typical Performance Characteristics

(Unless otherwise specified, $T_A = 25^\circ\text{C}$, $AV_{DD} = VP_{IN1}$ to $VP_{IN4} = 5.0\text{ V}$, $f_{OSC} = 2\text{ MHz}$)

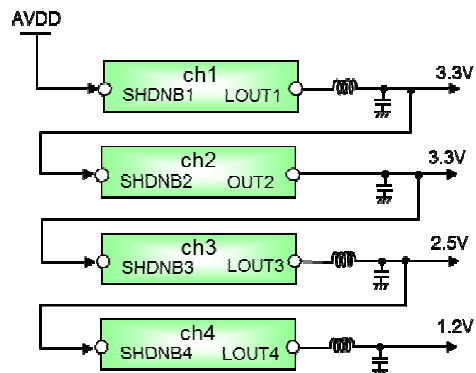
Efficiency vs. Output Current



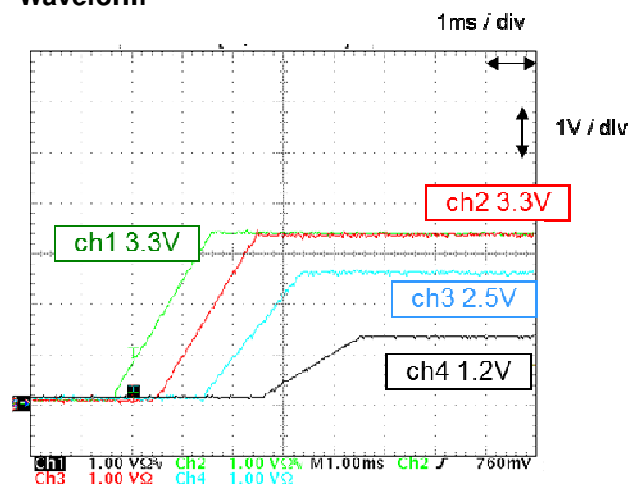
Start-up waveforms

Example 1 ch1(3.3V) ->ch2(3.3V) ->ch3(2.5V) ->ch4(1.2V)

Configuration

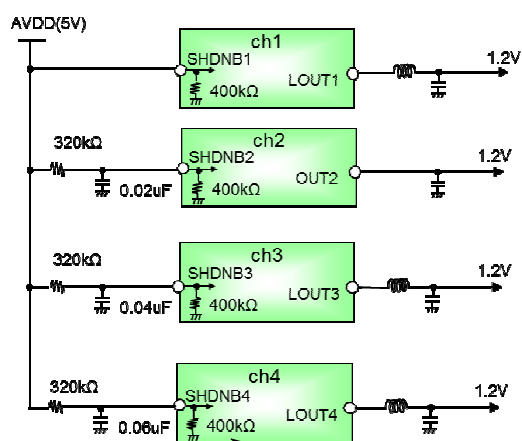


Waveform

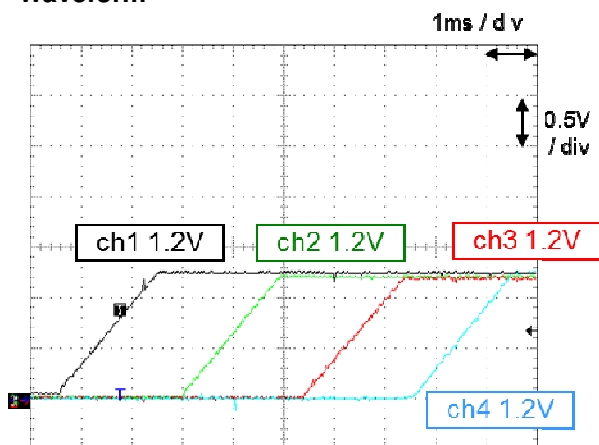


Example 2 ch1(1.2V) ->ch2(1.2V) ->ch3(1.2V) ->ch4(1.2V)

Configuration



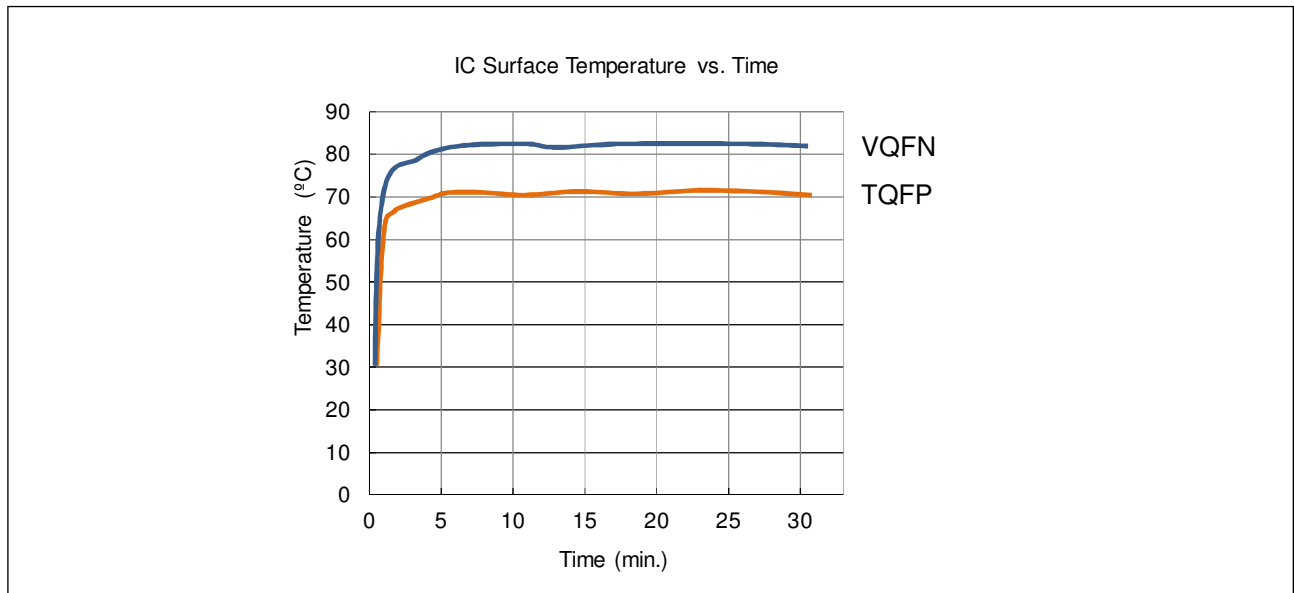
Waveform



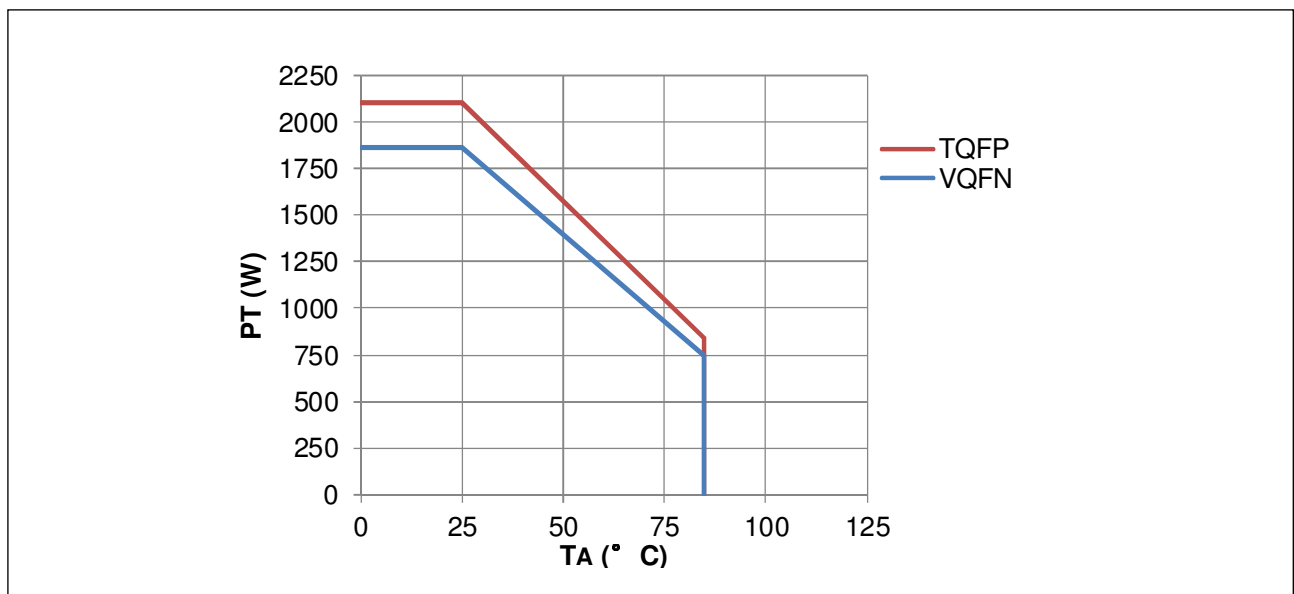
SHDNB pins have pull-down resistors (400kΩ). Please make sure that input voltage divided by external resistor on SHDNB pins shall not be lower than 1.4V.

IC Surface Temperature vs. Time

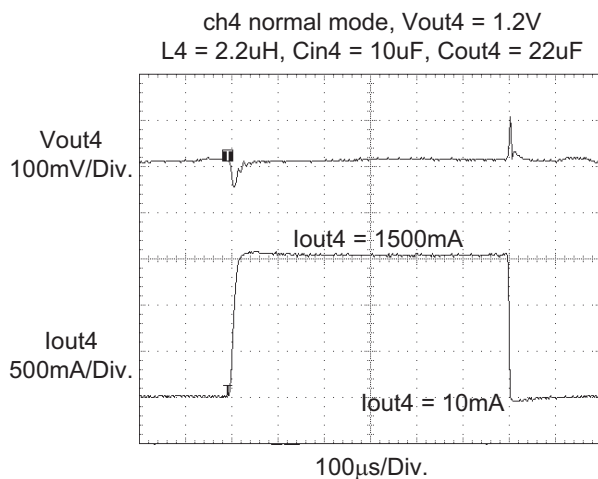
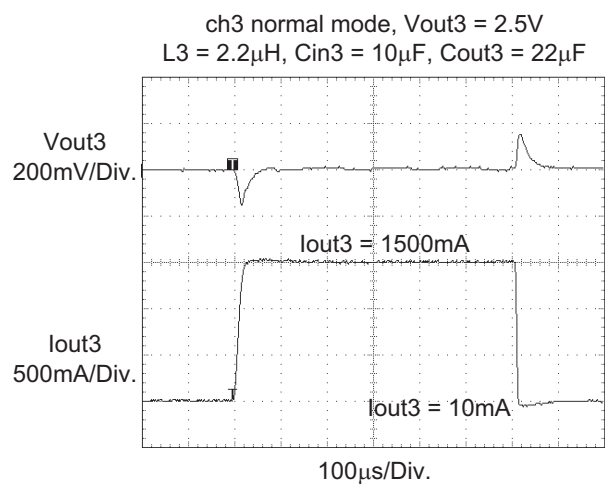
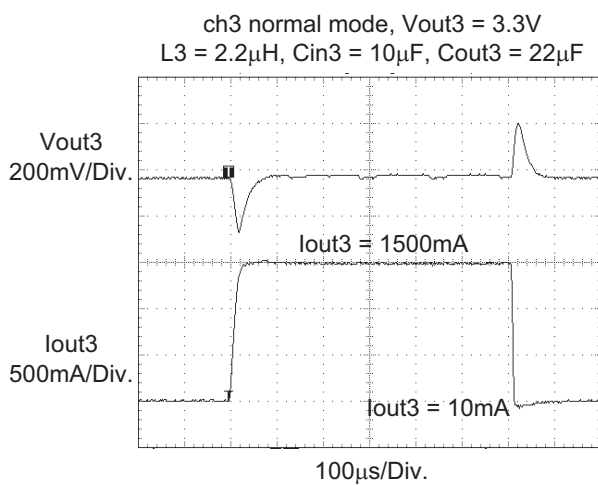
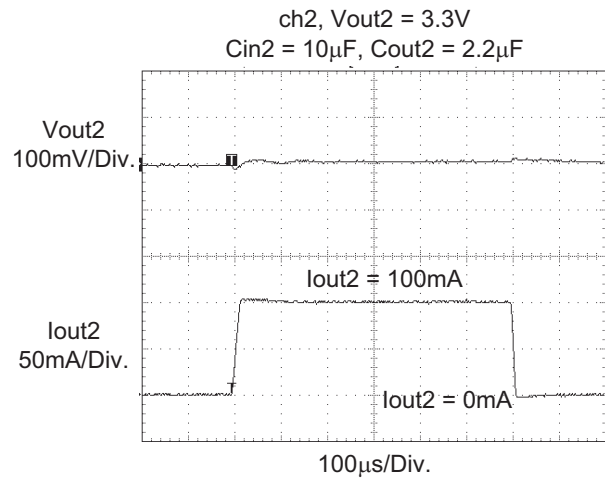
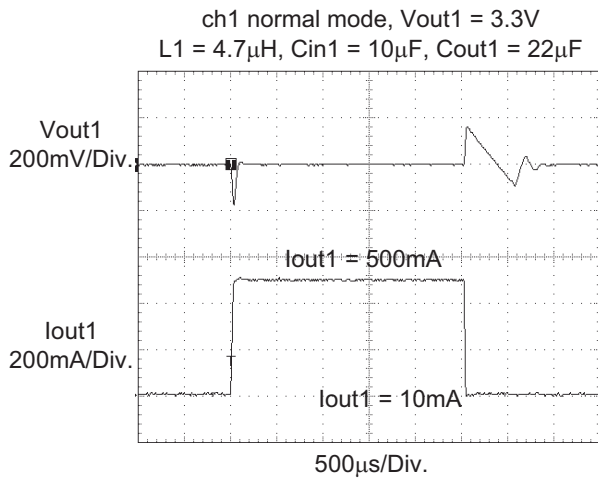
- All channel operating (normal mode)
- VIN=5V
- ch1: 3.3 V, 0.5 A ch2: 3.3 V, 0.1A ch3: 3.3 V, 1.5 A ch4: 1.2 V, 1.5 A
- T_A=25°C
- Measured on Renesas Evaluation board



Temperature Derating Curve



Load Transient Waveforms



Control Block

SHDNB0 to SHDNB4: ON/OFF Setting

| SHDNB0 | SHDNB1 | SHDNB2 | SHDNB3 | SHDNB4 | Common Circuit | ch1 | ch2 | ch3 | ch4 |
|--------|--------|--------|--------|--------|----------------|-----|-----|-----|-----|
| L | L or H | L or H | L or H | L or H | OFF | OFF | OFF | OFF | OFF |
| H | L | L | L | L | ON | OFF | OFF | OFF | OFF |
| H | H | L | L | L | ON | ON | OFF | OFF | OFF |
| H | L | H | L | L | ON | OFF | ON | OFF | OFF |
| H | L | L | H | L | ON | OFF | OFF | ON | OFF |
| H | L | L | L | H | ON | OFF | OFF | OFF | ON |
| H | H | H | H | H | ON | ON | ON | ON | ON |

Note: L: Low level, H: High level

Common Circuit: Reference voltage block, internal power supply block, oscillator block and so forth

OFF: circuit stand-by, ON: circuit operation status

SAVE: IC Low Power Mode Setting

| SAVE | IC Operation |
|------|--|
| L | Normal operation (ch1, ch3, ch4 operate at oscillation frequency set by RT) |
| H | Low power mode operation (ch1, ch3, ch4 operate at 15% oscillation frequency of normal operation) |

Note: L: Low level, H: High level

CTL4: ch4 Output Voltage Setting

| CTL4 | ch4 Output Voltage Setting |
|------|---|
| L | External resistor setting |
| H | Internal resistor setting (fixed 1.2 V) |

Note: L: Low level, H: High level

Output Status

V_{REG} , V_{REF} Pin Status

| SHDNB0 | V_{REG} | V_{REF} |
|--------|-----------|-----------|
| L | AGND | AGND |
| H | 2.4 V | 1.0 V |

Note: L: Low level, H: High level

ch1 to ch4 Output Pin Status

| SHDNB0 | SHDNB1 to SHDNB4 | ch1 | ch2 | ch3 | ch4 |
|--------|------------------|---------------------------------|---------------------------------|---------------------------------|--------------------------------|
| | | LOUT1 | OUT2 | LOUT3 | LOUT4 |
| L | L or H | HiZ (Discharge circuit, OFF) | AGND (Discharge circuit, ON) | HiZ (Discharge circuit, OFF) | |
| H | L | PGND (Discharge circuit, ON) | AGND (Discharge circuit, ON) | PGND (Discharge circuit, ON) | |
| | H | Pulse (VP_{IN1} or PGND) | ch2 (set voltage) | Pulse (VP_{IN3} or PGND) | Pulse (VP_{IN4} or PGND) |

Note: L: Low level, H: High level, HiZ: High impedance

PG1 Pin Status

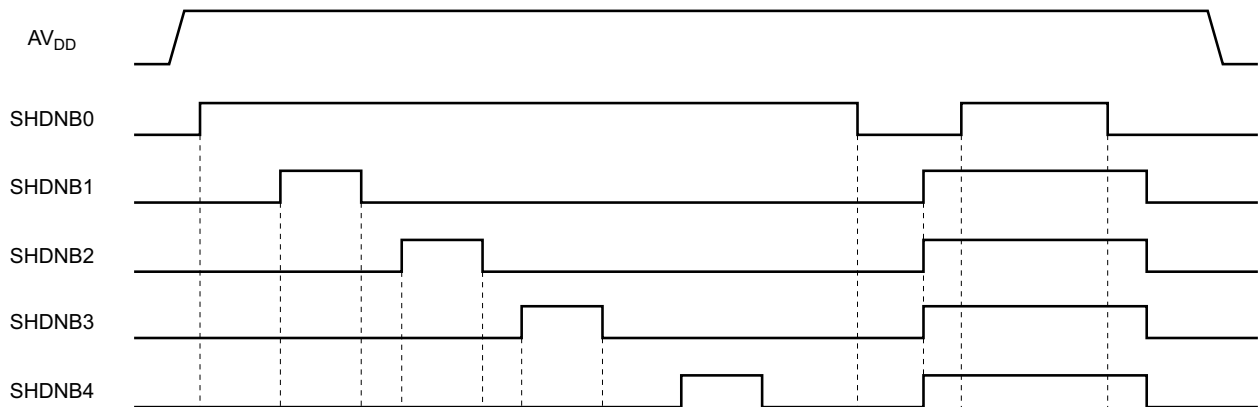
| IC Operation Status | | PG1 Output Status |
|---------------------|--|-------------------|
| SHDNB0 = L | | HiZ |
| SHDNB0 = H | The ch1 output voltage is under 90% of the set voltage | L |
| | The ch1 output voltage is over 90% of the set voltage | HiZ |

Note: L: Low level, HiZ: High impedance

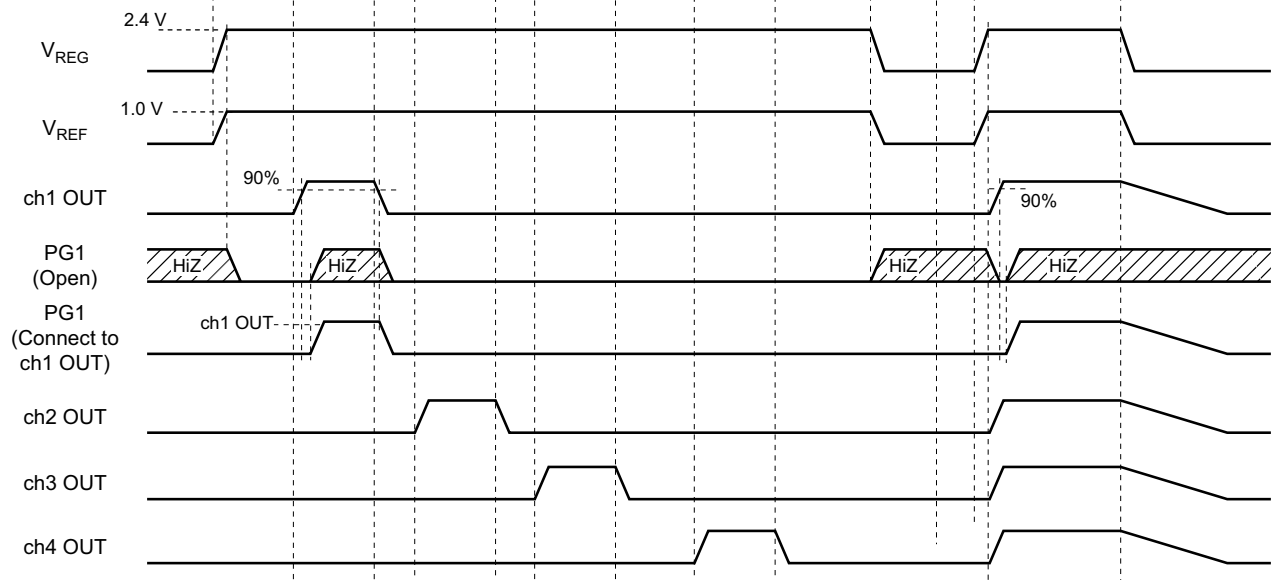
Caution: When using power good (PG1 pin), connect it to ch1 output.

Timing Chart

• Input



• Output



The output voltage of each channel can be turned on/off individually.

When SHDNB0 is set to OFF, the discharge circuit doesn't operate. (Naturally discharge)

Operation of Each Block (Overview)

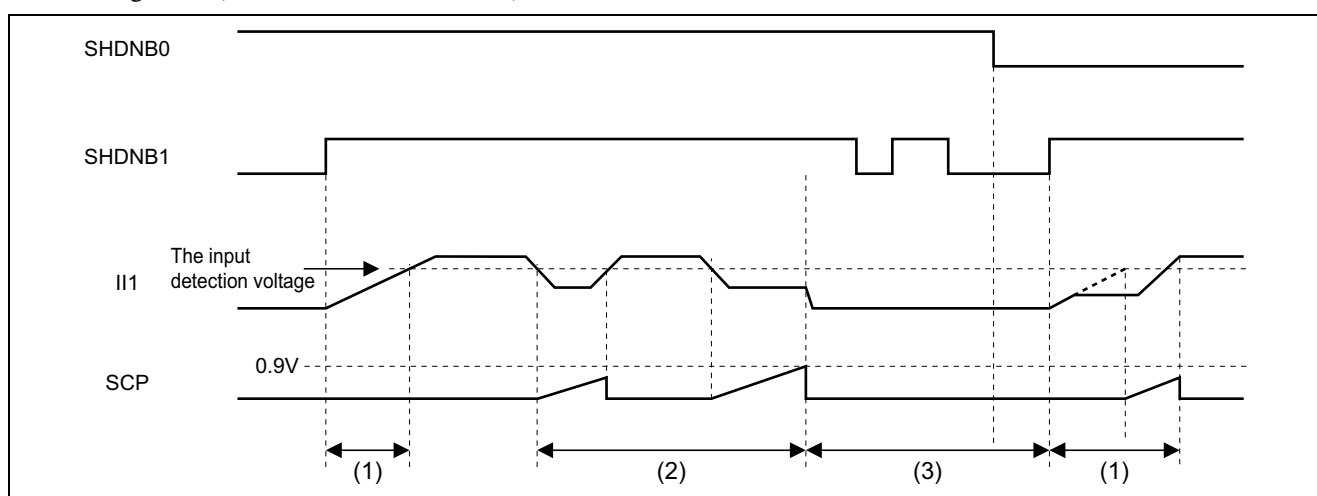
Short-Circuit Protection Circuit (ch1, ch3 and ch4)

When the voltage of ch1, ch3 and ch4 drops, the voltage of the E/A inverted input pin to which the output is being fed back also drops. If this inverted input pin voltage falls below the input detection voltage of the short-circuit protection circuit (under 75% of output voltage), the timer circuit starts operating and the capacitor connected to the SCP pin (CSCP) starts charging. When the voltage of the capacitor connected to the SCP pin reaches 0.9 V (TYP.), all the outputs are latched to OFF. At this time, common circuits (such as the reference voltage block, internal power supply block, and oscillator, etc.) continue operating.

As long as the voltage of any of the E/A inverted input pins of ch1 to ch4 is below the input detection voltage of the short-circuit protection circuit, the capacitor connected to the SCP pin continues charging.

When the short-circuit protection circuit is operating, to reset the latch circuit, either change the level of the SHDNB0 pin from high to low or drop the level of the power supply voltage (AV_{DD}) to the level below the operation stop voltage of the under voltage lockout circuit (1.7 V to 2.1 V).

- Timing Chart (when ch1 is short circuited)



(1) At starting

- A short circuit will not be detected while a channel is undergoing a soft start (that is, short-circuit protection is not triggered). If a short circuit occurs while a channel is operating, short-circuit protection will start after the soft start time elapses following startup.
- If a short circuit occurs in a channel that is operating while another channel is being soft-started, short-circuit protection will start immediately.

(2) Short-circuit protection operation

- If a short circuit is detected in any of channel 1, 3 and 4 (channels whose II pin voltage is lower than the input detection voltage except channels that are being soft-started), the capacitor connected to the SCP pin starts charging. If short circuits occur in multiple channels, the capacitor connected to the SCP pin continues to charge until the short-circuit state of all channels is canceled (that is, until the II pin voltage is restored over the input detection voltage).
- Once the SCP pin voltage reaches 0.9 V, output from all channels stops (and is latched to OFF).
- Common circuits (such as the reference voltage block, internal power supply block, and oscillator, etc.) continue operating.

(3) Cancelling short-circuit protection

- To reset the latch circuit, either change the level of the SHDNB0 pin from high to low, or drop the level of the power supply voltage (AV_{DD}) to the operation stop voltage of the under voltage lockout circuit (1.7 V to 2.1 V).

Thermal Shutdown Circuit (Timer Latch Type)

After overheating has been detected (shutdown temperature: 150°C or higher), the timer circuit starts operating and the capacitor connected to the SCP pin (CSCP) starts charging. When the voltage of the capacitor connected to the SCP pin reaches 0.9 V (TYP.), all the outputs are latched to OFF (as same as SCP). Common circuits (such as the reference voltage block, internal power supply block, and oscillator, etc.) continue operating.

When the thermal shutdown circuit is operating, to reset the latch circuit, either change the level of the SHDNB0 pin from high to low, or drop the level of the power supply voltage (AV_{DD}) to the operation stop voltage of the under voltage lockout circuit (1.7 V to 2.1 V).

Under Voltage Lockout Circuit (Auto Recovery Type)

(1) Under voltage lockout operation

When the power supply voltage (AV_{DD}) falls to the operation stop voltage (1.7 V to 2.1 V), output from all channels stops. Common circuits (such as the reference voltage block, internal power supply block, and oscillator, etc.) continue operating.

(2) Restoring output

Once AV_{DD} voltage is restored to the operation start voltage (1.9 V to 2.3 V), the under voltage lockout operation is canceled and output automatically resumes. The output voltage cannot be restored while the under voltage lockout circuit is operating, not even by manipulating the SHDNB0 pin.

Current Limiting

Ch1, ch3, and ch4 operate under the current control mode. If an overcurrent occurs, the current is limited on a pulse-by-pulse basis. If the current sensor detects an overcurrent, the current is limited and the switching operation of the Power MOSFET in the output stage stops until the next cycle.

When the current is limited, the output voltage of the channel on which the overcurrent occurred drops. If the II pin voltage falls below the input detection voltage, the short-circuit protection circuit starts operating.

Reference data (Unless otherwise specified, $T_A = 25^\circ\text{C}$, $AV_{DD} = VP_{IN1}$ to $VP_{IN4} = 5.0\text{ V}$, $f_{OSC} = 2\text{ MHz}$)

| Item | | Symbol | Min | Typ | Max | unit | Measurement condition |
|---------------------|--------------------------|----------------|-----|-----|-----|------|------------------------|
| Current limit value | ch1 Current limet | I_{LIM1} | — | 1.6 | — | A | ch1OUT = 3.3V |
| | ch3, ch4 Current limet 1 | I_{LIM34_1} | — | 2.6 | — | A | ch3OUT = ch4OUT = 3.3V |
| | ch3, ch4 Current limet 2 | I_{LIM34_2} | — | 2.1 | — | A | ch3OUT = ch4OUT = 1.2V |

Note: These data are for reference and not guaranteed as specifications.

Over Current Protection (ch2)

Ch2 have a fold back type current protection circuit. If load current exceeds 150 mA, protection operation is started and load current is limited (output short-circuit current: 80 mA).

Low Power Mode

This IC has the low power mode. By setting SAVE pin into a high level, the oscillation frequency of a switching regulator (ch1, ch3, ch4) is dropped on 15% oscillation frequency of normal operation, and the power consumption of the IC is reduced.

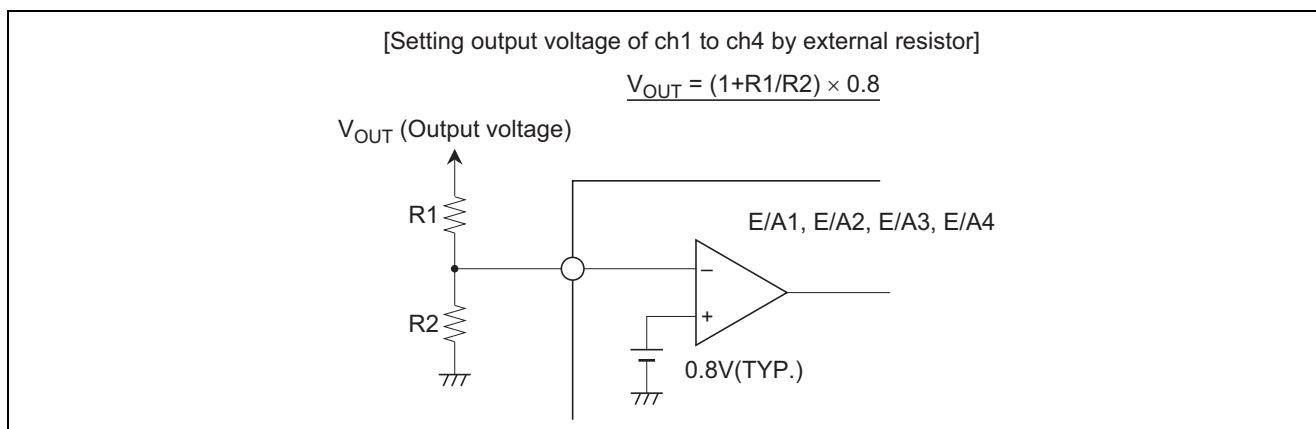
When switching to the low power mode, please switch the mode in a condition that the output current of a switching regulator (ch1, ch3, ch4) is below 100 mA.

Please be cautious of increasing the ripple voltage of each channel at the low power mode.

Advance on Designing

Setting Output Voltage (When the output voltage is set by external resistor)

The output voltage settings are shown in the figures below. The output voltage can be calculated by using the equations shown in these figures.



Setting Oscillation Frequency

The oscillation frequency (f_{OSC}) can be arbitrarily set by the timing resistance (R_T) connected to the RT pin.

$$\text{Approximate equation: } f_{OSC}[\text{MHz}] = -0.107 \times R_T[\text{k}\Omega] + 3.05$$

Calculating the Soft Start Time

The soft start time (t_{SS}) can be arbitrarily set by the resistance (R_{SS}) connected to the SS pin.

$$\text{Approximate equation: } t_{SS}[\text{ms}] = 1.8 \times R_{SS}[\text{M}\Omega] + 0.24$$

Note: Soft start time is the same by all channels.

Calculating the Delay Time of the Short-circuit Protection Circuit

The following approximate expression is for calculating the delay time t_{DLY} of the short-circuit protection circuit.

The delay time of the short-circuit protection circuit (t_{DLY}) can be arbitrarily set by the capacitor (C_{SCP}) connected to the SCP pin.

$$\text{Approximate equation: } t_{DLY}[\text{s}] = 0.9 \times C_{SCP} [\mu\text{F}]$$

Pin handling when Short-circuit Protection Circuit is not used

When the short-circuit protection circuit is not used, connect the SCP pin to the AGND pin. At this time, closely monitor heating because the overheat protection circuit does not operate.

Handling of pins when not used

Connect unused pins as below.

Always connect AVDD pin, VPIN1 pin, VPIN2 pin, VPIN3 pin and VPIN4 pin with power supplies, and connect PGND1 pin, PGND3 pin, PGND4 pin and AGND with the ground.

When ch1 is not used:.

| Pin number | Pin name | Connection |
|------------|-------------------|--|
| 31 | SHDNB1 | AGND |
| 2 | VP _{IN1} | AV _{DD} , or VP _{IN} of other ch |
| 1 | LOUT1 | PGND |
| 3 | PGND1 | PGND |
| 4 | II1 | AGND |

When ch2 is not used:

| Pin number | Pin name | Connection |
|------------|-------------------|--|
| 30 | SHDNB2 | AGND |
| 9 | VP _{IN2} | AV _{DD} , or VP _{IN} of other ch |
| 10 | OUT2 | AGND |
| 8 | II2 | AGND |

When ch3 is not used:

| Pin number | Pin name | Connection |
|------------|-------------------|--|
| 26 | SHDNB3 | AGND |
| 18 | VP _{IN3} | AV _{DD} , or VP _{IN} of other ch |
| 17 | LOUT3 | PGND |
| 19 | PGND3 | PGND |
| 20 | II3 | AGND |

When ch4 is not used:

| Pin number | Pin name | Connection |
|------------|-------------------|--|
| 25 | SHDNB4 | AGND |
| 23 | VP _{IN4} | AV _{DD} , or VP _{IN} of other ch |
| 24 | LOUT4 | PGND |
| 22 | PGND4 | PGND |
| 21 | II4 | AGND |
| 6 | CTL4 | AGND |

When PG1 pin is not used

| Pin number | Pin name | Connection |
|------------|----------|------------|
| 5 | PG1 | AGND |

Inductor selection

It is recommended to choose an inductor whose ripple current (ΔI_L) becomes 20 to 40 % of $I_{out(max)}$.

When ΔI_L increases, inductor current peak rises, so ripple of V_{out} gets larger and power loss increases. But, large inductor is required to lower ΔI_L .

ΔI_L can be calculated by an equation below.

$$\Delta I_L = (V_{in} - V_{out}) / L \times V_{out} / V_{in} \times 1 / f_{sw}$$

f_{sw} : Switching frequency of DCDC, 1.3MHz to 2MHz

Peak current of inductor (I_{Lpeak}) can be calculated by an equation below.

$$I_{Lpeak} = I_{out(max)} + \Delta I_L / 2$$

Choose an inductor whose saturation current is higher than I_{Lpeak} .

Inductor Example

| ch | Output Current | Inductor | Manufacturer | Inductance (uH) | I _{TEMP} (A) | I _{SAT} (A) | Size (LxWxT, mm) |
|-----------|----------------|------------------|--------------|--------------------|-----------------------|----------------------|---------------------|
| ch1 | less than 0.5A | CPL2512T4R7M | TDK | 4.7 | 0.65 | 0.65 | 2.5x1.5x1.2 |
| | | NRS2012T4R7MGJ | TAIYO YUDEN | 4.7 | 0.82 | 0.76 | 2x2x1.2 |
| | | 74479787247A | WURTH | 4.7 | 1.5 | 0.27 | 2.5x2x1 |
| | | 744028004 | WURTH | 4.7 | 0.85 | 0.7 | 2.8x2.8x1.1 |
| ch3 | less than 1A | VLS201612ET-2R2M | TDK | 2.2 | 1.15 | 1.05 | 2x1.6x1.2 |
| ch4 | | NRS2012T2R2MGJ | TAIYO YUDEN | 2.2 | 1.37 | 1.35 | 2x2x1.2 |
| 744029002 | | WURTH | 2.2 | 1.5 | 1.15 | 2.8x2.8x1.35 | |
| ch4 | 1A to 1.5A | LQH44PN2R2MP0 | MURATA | 2.2 | 1.8 | 2.5 | 4x4x1.65 |
| | | NRS4018T2R2MDGJ | TAIYO YUDEN | 2.2 | 2.2 | 3 | 4x4x1.8 |
| | | 744025002 | WURTH | 2.2 | 1.8 | 2.4 | 2.8x2.8x2.8 |

Note I_{TEMP} : Rated current by temperature rising

I_{SAT} : Rated current by inductance loss

These inductors are examples. About inductor detail, contact each manufacturer.

Output capacitor selection

Each channel of RAA23040x has a phase compensation circuit which is optimized to each operation. In order to operate stably with the phase compensation, connect the output capacitor :

Switching Regulator (ch1, ch3, ch4) : over 22uF

LDO (ch2) : over 2.2uF

Ceramic capacitor can be used for output capacitor. It has low ESR, so VOUT ripple is decreased.

VOUT ripple (ΔV_{rpl}) can be calculated by an equation below.

$$\Delta V_{rpl} = \Delta I_L \times (ESR + 1 / (8 \times C_{out} \times f_{sw}))$$

Input capacitor selection

Recommended input capacitor of switching regulator can be calculated by an equation below. Connect the capacitor that value is over calculated one.

$$C_{in} > (I_{out(max)} \times V_{out} / V_{in}) / (\Delta V_{in} \times f_{sw})$$

About LDO, connect the capacitor that value is over 1uF.

Notes on Use

Condition where Protection Circuits do not operate

When the SCP pin is connected to the AGND pin, the short-circuit protection circuit and thermal shutdown circuit do not operate.

Pin Connection

Be sure to apply the same voltage to AV_{DD} pin and VP_{IN} pin (except VP_{IN2}).

VP_{IN2} Input Voltage

VP_{IN2} input voltage should be same or less than AV_{DD}.

PG1 Connection

When using power good (PG1 pin), connect it to ch1 output. If PG1 is connected to AV_{DD}, PG1 outputs high (AV_{DD}) when SHDNB0 is low (because PG1 is high impedance when SHDNB0 is low).

Actual Pattern Wiring

To actually perform pattern wiring, separate the ground of the control signals from the ground of the power signals, so that these signals do not have a common impedance as much as possible. In addition, lower the high-frequency impedance by using a capacitor, so that noise is not superimposed on the V_{REF} pin, V_{REG} pin.

Connection of Exposed PAD (only TQFP package)

TQFP package has an exposed pad on the bottom to improve radiation performance. On the mounting board, connect this exposed pad to AGND.

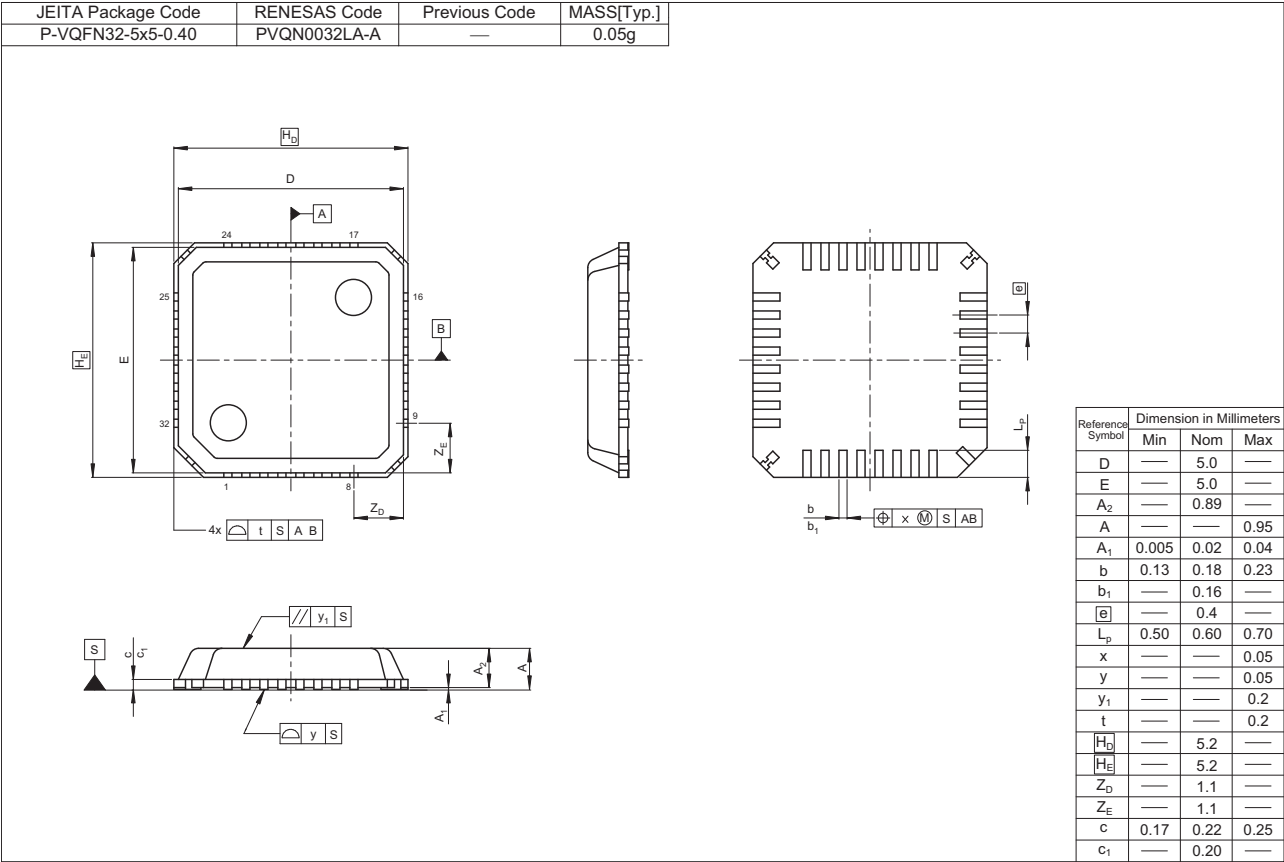
Fixed Usage of Control Input Pin

When using fixed input pins SHDNB0 to SHDNB4, CTL4 and SAVE input pins, connect each input to the pins listed below.

| Input Pin | Connect Pin | |
|-----------|--------------------|---------------------|
| | Fixed to Low Level | Fixed to High Level |
| SHDNB0 | AGND | AV _{DD} |
| SHDNB1 | AGND | AV _{DD} |
| SHDNB2 | AGND | AV _{DD} |
| SHDNB3 | AGND | AV _{DD} |
| SHDNB4 | AGND | AV _{DD} |
| CTL4 | AGND | AV _{DD} |
| SAVE | AGND | AV _{DD} |

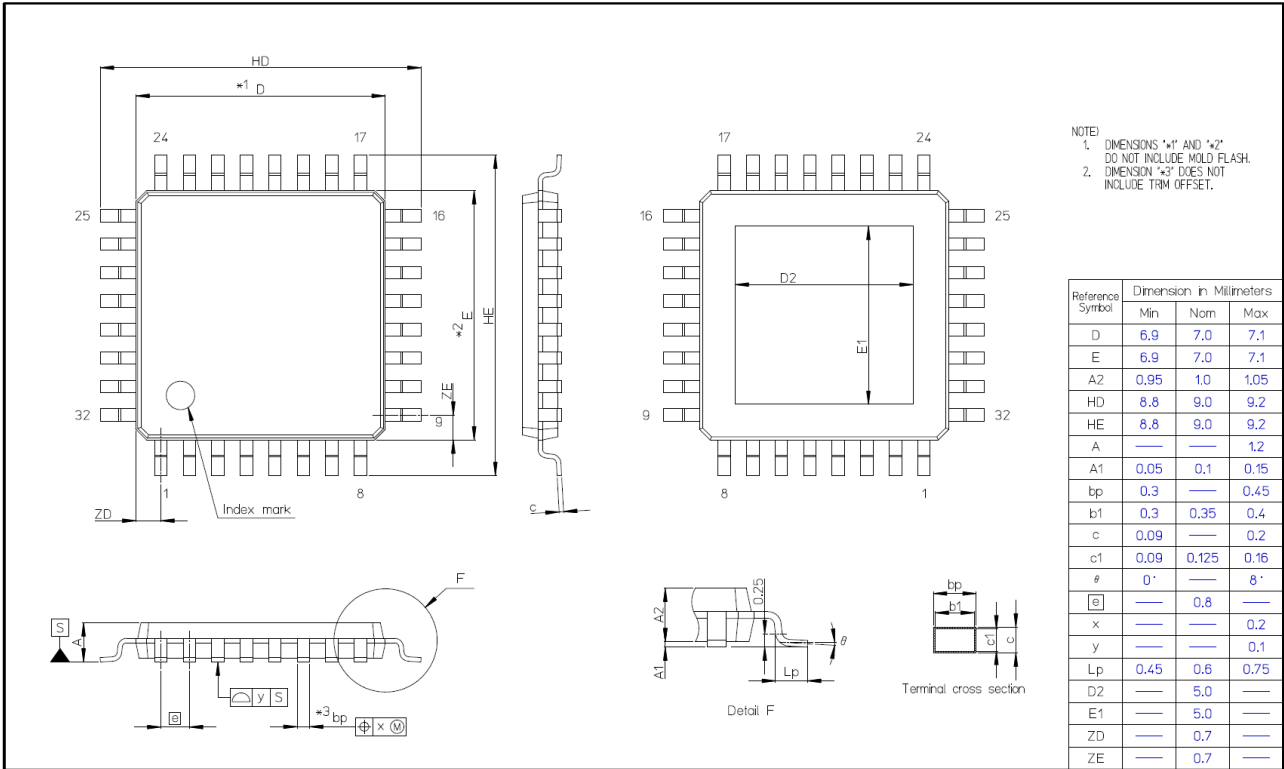
Package Dimensions

32-pin VQFN 5 mm × 5 mm 0.4 mm pitch



32-pin TQFP 7 mm × 7 mm 0.8 mm pitch

| JEITA Package Code | RENESAS Code | Previous Code | MASS[Typ.] |
|--------------------|--------------|---------------|------------|
| P-HTQFP32-7x7-0.80 | PTQP0032GA-A | 32P6X-A | 0.14g |



Revision History

RAA23040x Data Sheet

| Rev. | Date | Description | |
|------|--------------|-------------|---|
| | | Page | Summary |
| 1.01 | Oct 18, 2012 | - | First Edition issued |
| 1.02 | Jul 09, 2013 | 1 | Changed package name from LQFP to TQFP. Added packing unit. |
| | | 5 | Added Pin Configuration of 32-pin TQFP. |
| | | 7 | Added Total power dissipation and Board specification. |
| | | 9 | Changed Short-circuit source current from Min 0.7uA to 0.6uA and Max 1.3uA to 1.4uA. |
| | | 10 | Changed Output short-circuit current from Typ 40mA to 80mA. Added condition of Input regulation, Load regulation and Output short-circuit current. |
| | | 12 | Added start-up waveforms. |
| | | 13 | Added input voltage VIN condition. Changed output voltage/current condition. Added TQFP product's data. Added Temperature Derating Curve. |
| | | 16 | Changed Output Pin Status of ch2 at SHDNB0=L from HiZ to GND. |
| | | 19 | Added Reference data of Current limit value. Changed Output short-circuit current of Over Current Protection (ch2) from Typ 40mA to 80mA. |
| | | 21 | Added Handling of pins when not use. |
| | | 22 | Added Inductor selection |
| | | 23 | Added Output capacitor selection and Input capacitor selection. |
| | | 24 | Added Connection of Exposed PAD. |
| | | 26 | Added Package Dimensions of TQFP package. |
| | | | |

NOTES FOR CMOS DEVICES

- (1) **VOLTAGE APPLICATION WAVEFORM AT INPUT PIN:** Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (MAX) and V_{IH} (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (MAX) and V_{IH} (MIN).
- (2) **HANDLING OF UNUSED INPUT PINS:** Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) **PRECAUTION AGAINST ESD:** A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) **STATUS BEFORE INITIALIZATION:** Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) **POWER ON/OFF SEQUENCE:** In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) **INPUT OF SIGNAL DURING POWER OFF STATE:** Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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